Efficient Low-Noise Three Port X-Band FET Oscillator Using Two Dielectric Resonators

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A new, simple to realize, X band, 3 port stable FET oscillator is presented. The oscillator using 2 identical dielectric resonators as oscillator circuit elements, operates at 8.53 GHz, has an overall efficiency of 22% and FM noise better than 0.2 Hz/ /spl radic/Hz at 10 KHz from carrier.

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